

Silicon PNP Power Transistors

2SB772

DESCRIPTION

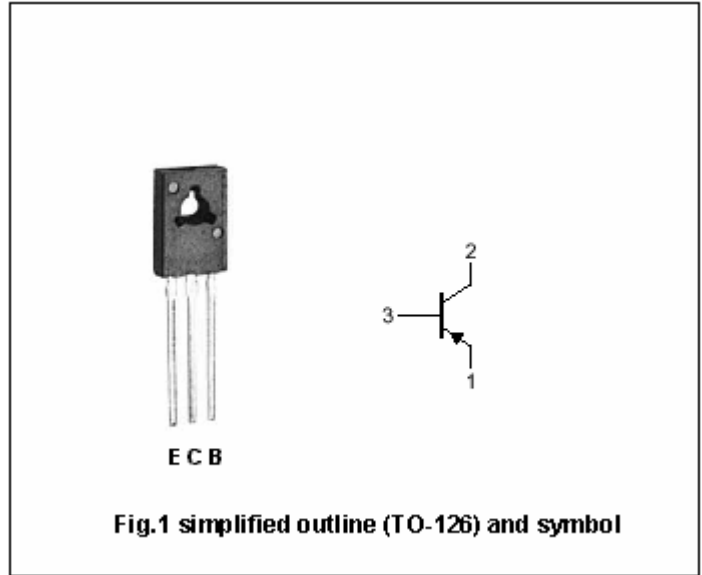
- With TO-126 package
- Complement to type 2SD882

APPLICATIONS

- Suited for the output stage of 3 watts audio amplifier ,voltage regulator ,DC-DC converter and relay driver

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

**Absolute maximum ratings(Ta=25□)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-40	V
V _{CEO}	Collector-emitter voltage	Open base	-30	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current (DC)		-3	A
I _{CM}	Collector current-Peak		-7	A
P _D	Total power dissipation	T _a =25□	1.0	W
		T _C =25□	10	
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-55~150	□

Silicon PNP Power Transistors

2SB772

CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA ; I _B =0	-30			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-2.0A ; I _B =-0.2A		-0.3	-0.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-2.0A ; I _B =-0.2A		-1.0	-2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-30V ; I _E =0			-1.0	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-3V ; I _C =0			-1.0	μA
h _{FE-1}	DC current gain	I _C =-20mA ; V _{CE} =-2V	30			
h _{FE-2}	DC current gain	I _C =-1A ; V _{CE} =-2V	60		400	
f _T	Transition frequency	I _C =-0.1A ; V _{CE} =-5V		80		MHz
C _{OB}	Collector output capacitance	I _E =0 ; f=1MHz ; V _{CB} =-10V		55		pF

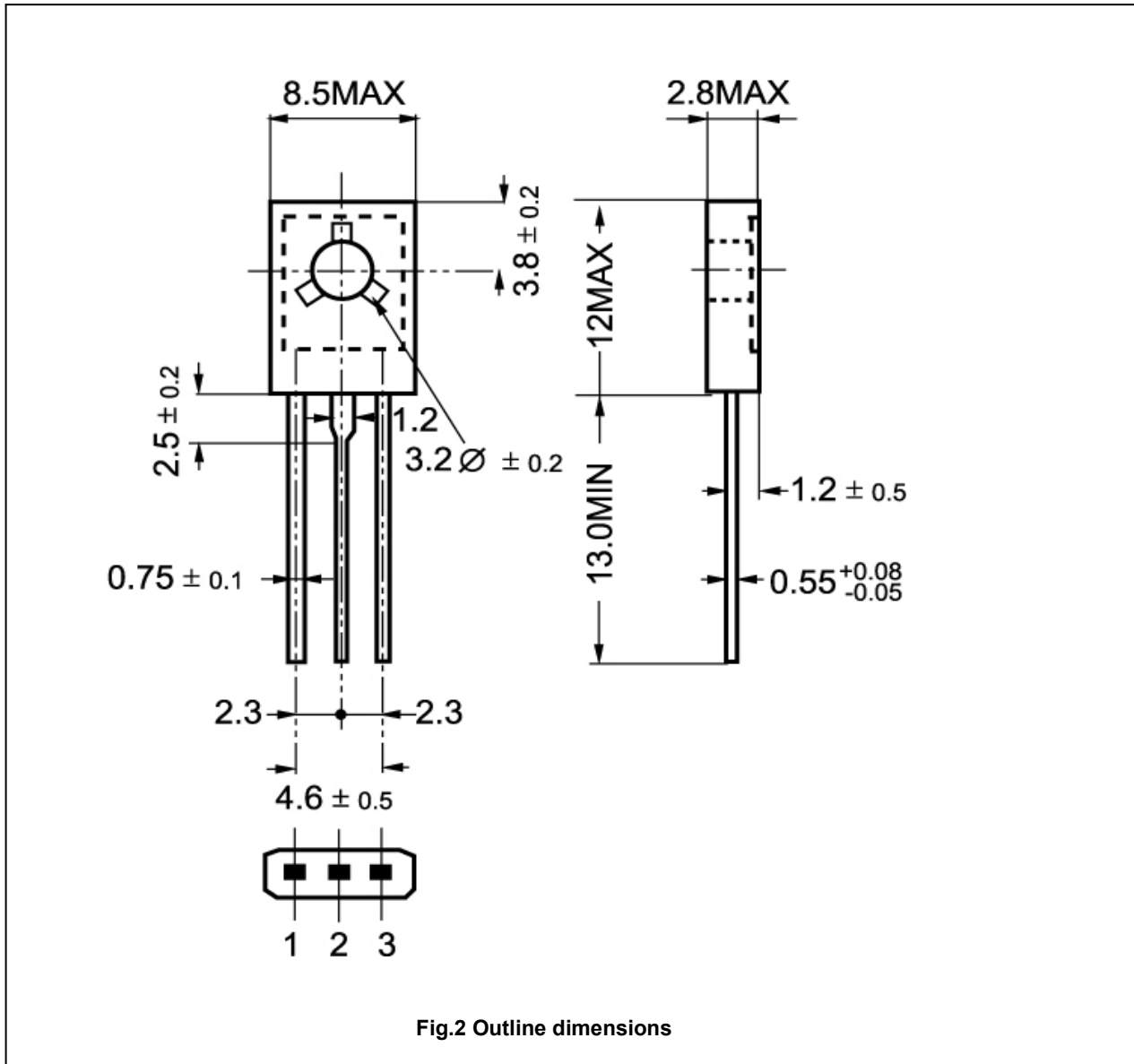
◆ h_{FE-2} Classifications

R	Q	P	E
60-120	100-200	160-320	200-400

Silicon PNP Power Transistors

2SB772

PACKAGE OUTLINE



Silicon PNP Power Transistors

2SB772

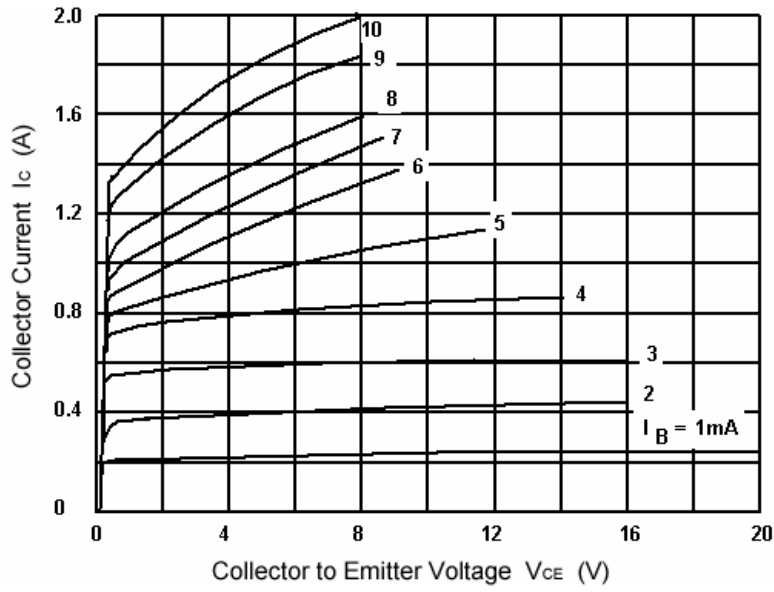


Fig.3 Static Characteristic

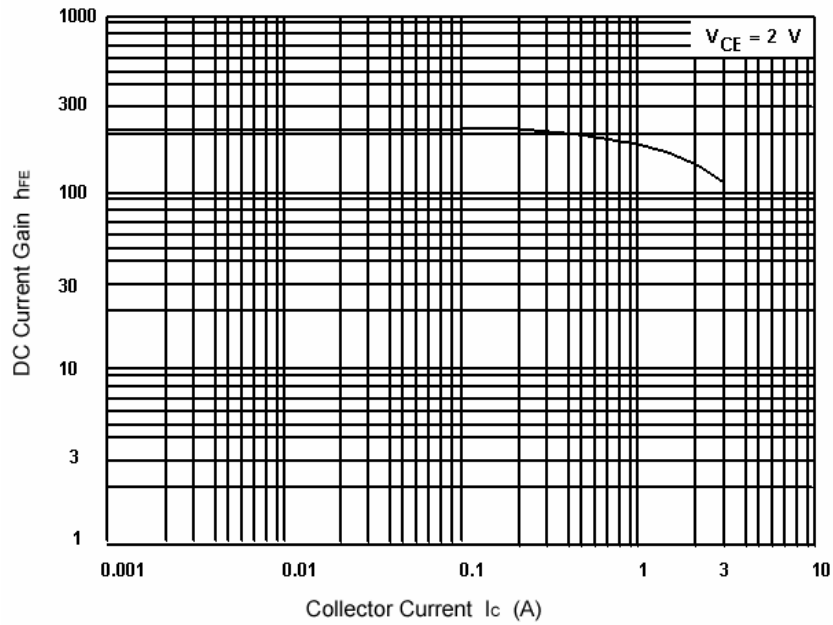


Fig.4 DC current Gain

Silicon PNP Power Transistors

2SB772

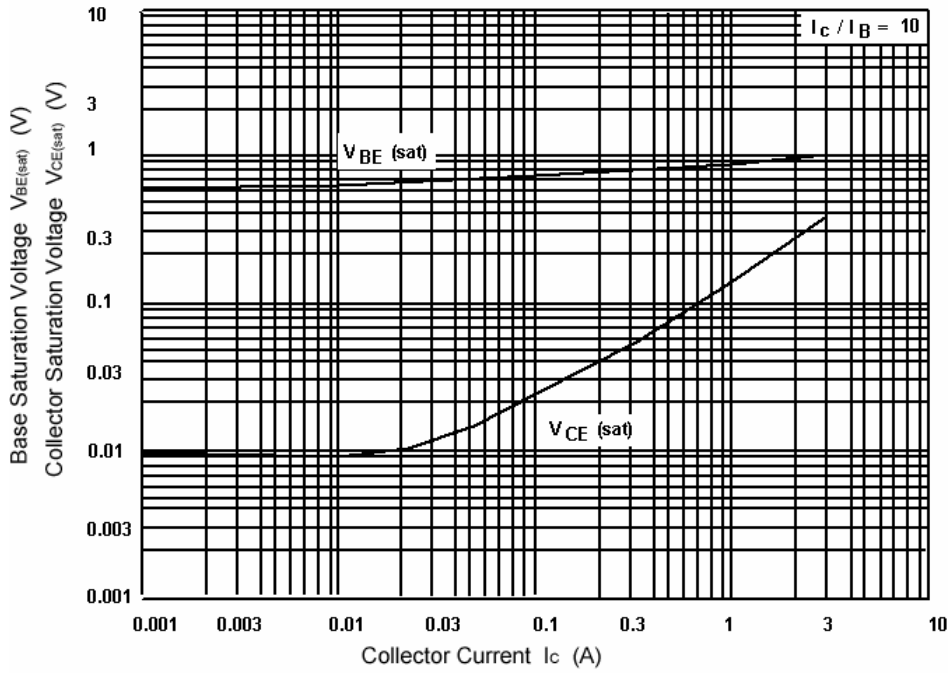


Fig.5 Base-Emitter Saturation Voltage
Collector-Emmitter Saturation Voltage

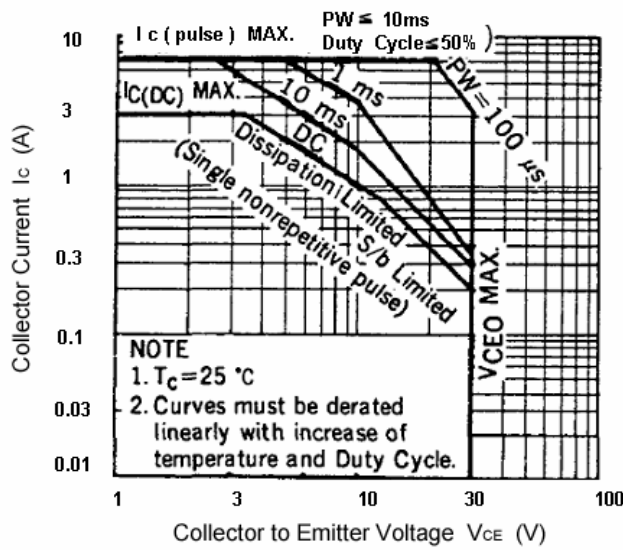


Fig.6 Safe Operating Area